

Moulded Module Assembly

PBT 91 / PBH 91

(Thyristor - Thyristor Module /
Thyristor - Diode Module)



Technical Data

Typical applications : DC Motor control, Temperature control, Professional light dimming.

Type No.		V_{RRM} (Volts)	V_{RSM} (Volts)
PBT 91/04	PBH 91/04	400	500
PBT 91/06	PBH 91/06	600	700
PBT 91/08	PBH 91/08	800	900
PBT 91/10	PBH 91/10	1000	1100
PBT 91/12	PBH 91/12	1200	1300
PBT 91/14	PBH 91/14	1400	1500
PBT 91/16	PBH 91/16	1600	1700

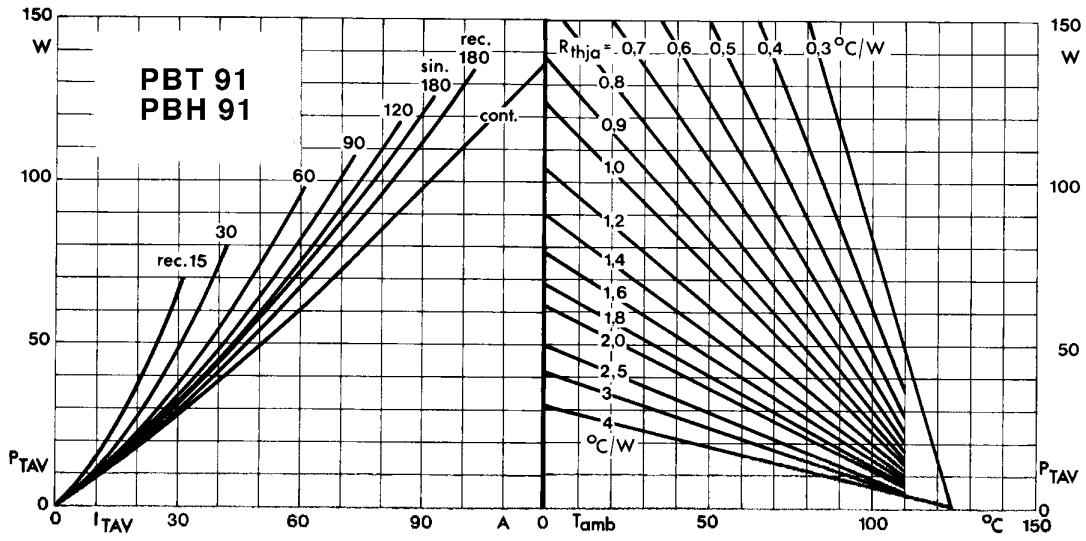
Features

- Heat transfer through ceramic isolated Cu base
- Isolation between contacts & mounting base is 2.5KV(rms)
- Weight 120 gm (Approx)

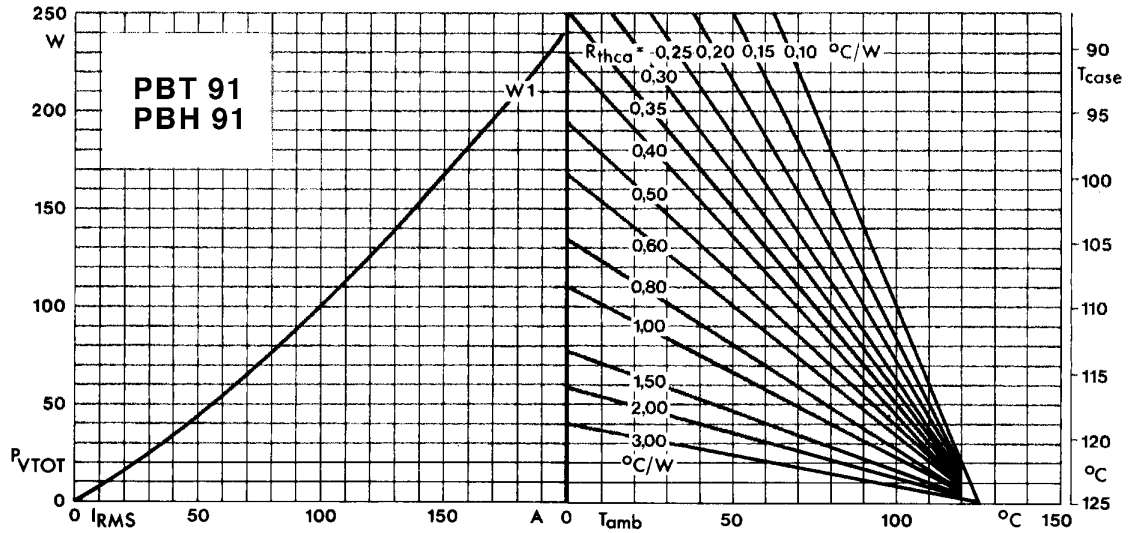
dv/dt 200V/μs typ. (Higher upto 1000V/μs available on request)

Symbol	Conditions	Values
$I_{F(AV)}$	Sin 180 ; T _{case} = 90 °C	90 A
$I_{(RMS)}$	Absolute maximum	180 A
I_{TSM}	T _{vj} = 25 °C; Half Sine; 10 ms; 0V _{RRM}	2000 A
	T _{vj} = 125 °C; Half Sine; 10 ms; 0V _{RRM}	1750 A
I ² t	T _{vj} = 25 °C; Half Sine; 10 ms	20000 A ² s
	T _{vj} = 125 °C; Half Sine; 10 ms	15000 A ² s
di/dt	T _{vj} = 125 °C	100 A/μs
tq	T _{vj} = 125 °C; di/dt=10A/μs; dv/dt=50V/μs reapplied	typ. 100μs
I _H	T _{vj} = 25 °C	(typ. 150/Max.250)mA
I _L	T _{vj} = 25 °C; R _G = 33	(typ. 300/Max.600)mA
V _T	T _{vj} = 25 °C ; I _T = 300 A	1.65V max
V _O	T _{vj} = 125 °C	0.9V
R _θ	T _{vj} = 125 °C	2.0 m
I _{DRM} /I _{RRM}	T _{vj} = 125 °C	20 mA max
V _{GT}	T _{vj} = 25 °C ; D.C. value	3V
I _{GT}	T _{vj} = 25 °C ; D.C. value	150 mA
R _{th(j-c)}	cont. ; per thyristor/ per module Sin. 180 ; per thyristor/ per module rec. 120 ; per thyristor/ per module	0.28/0.14 °C/W 0.30/0.15 °C/W 0.32/0.16 °C/W
R _{th(c-h)}		0.20/0.10 °C/W
T _{vj}		+ 125 °C
T _{stg}		-40.....+ 125 °C
V _{ISOL}	A.C. 50 Hz: r.m.s.; 1sec	3.0 KV
	A.C. 50 Hz: r.m.s.; 1min	2.5 KV

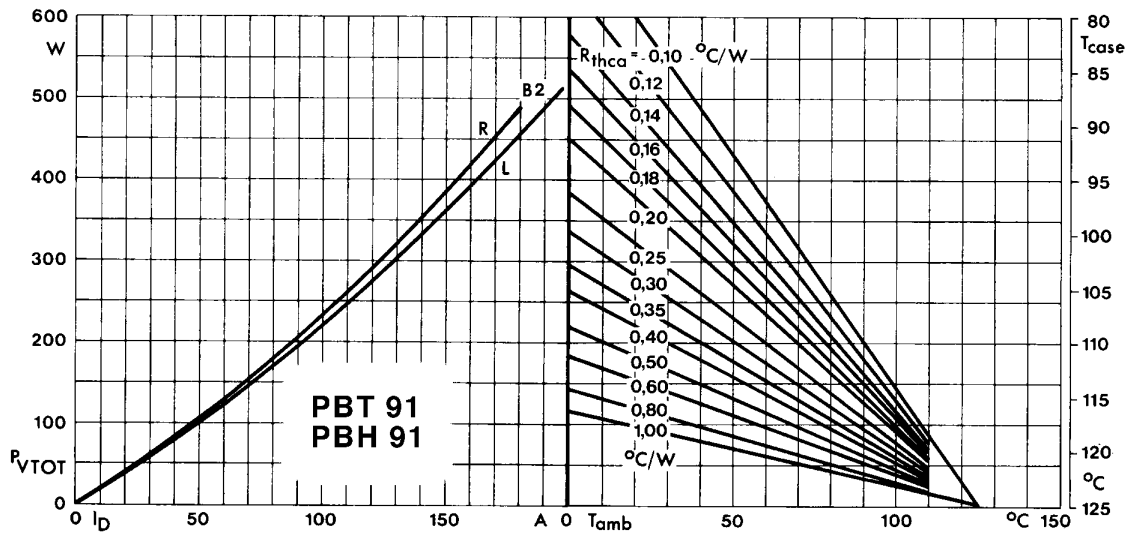




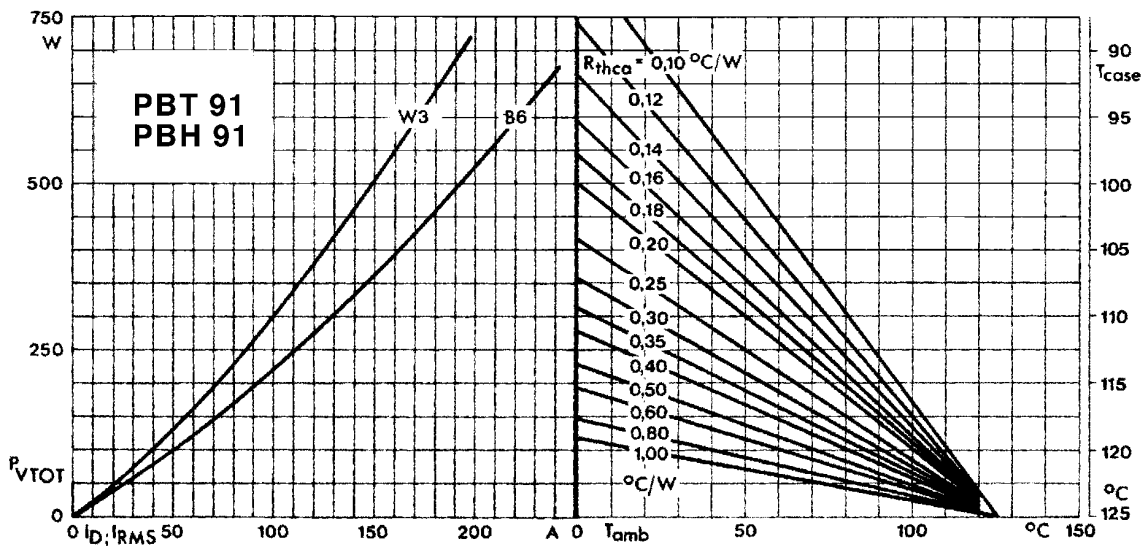
Power dissipation per thyristor vs. on-state current and ambient temperature



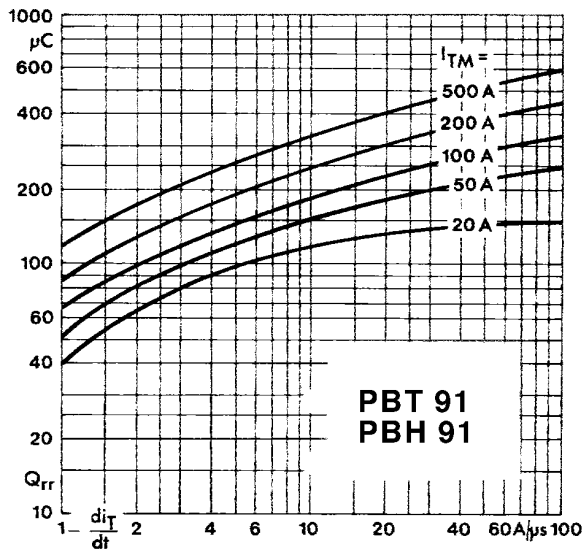
Power dissipation per module vs. rms current and case temperature



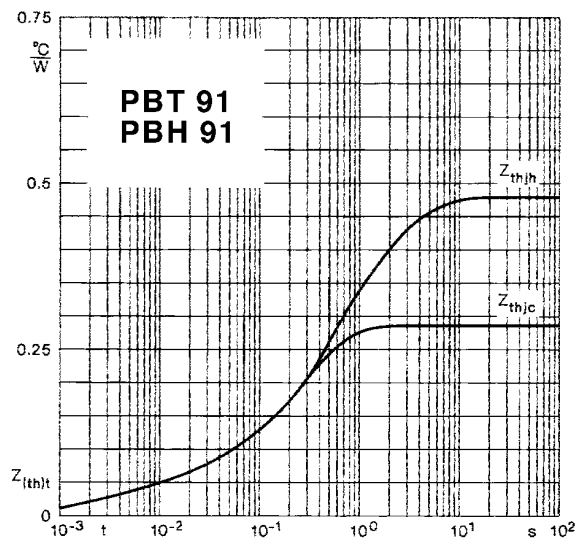
Power dissipation of two modules vs. direct current and case temperature



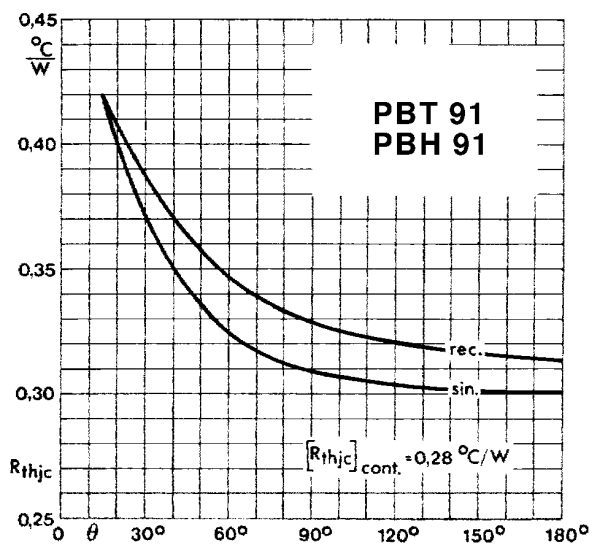
Power dissipation of three modules vs. direct and rms current and case temperature



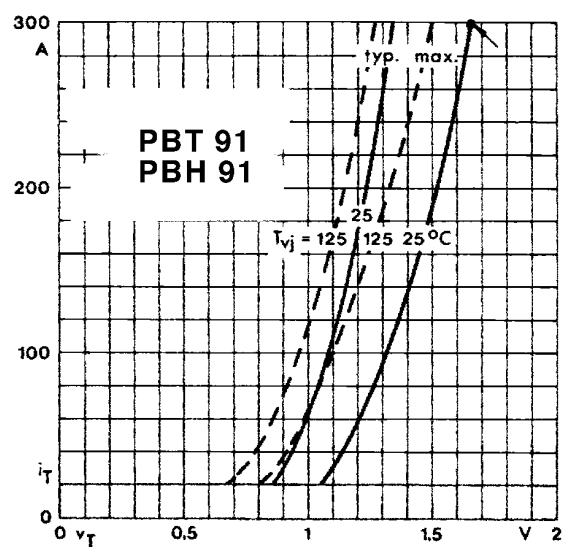
Recovered charge vs. current decrease



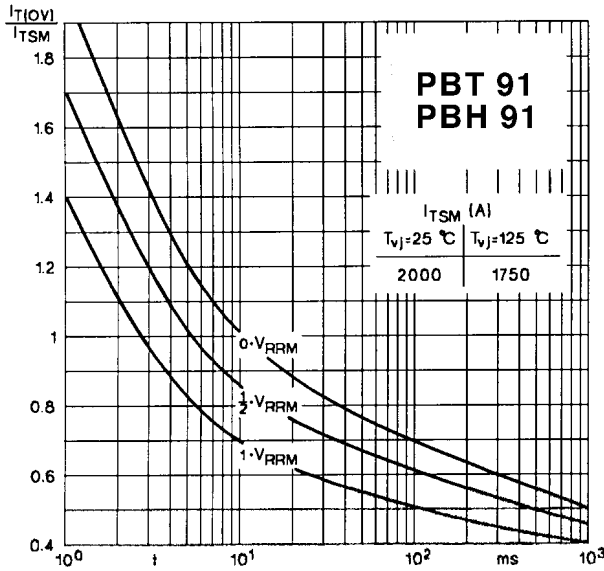
Transient thermal impedance vs. time



Thermal resistance vs. conduction angle

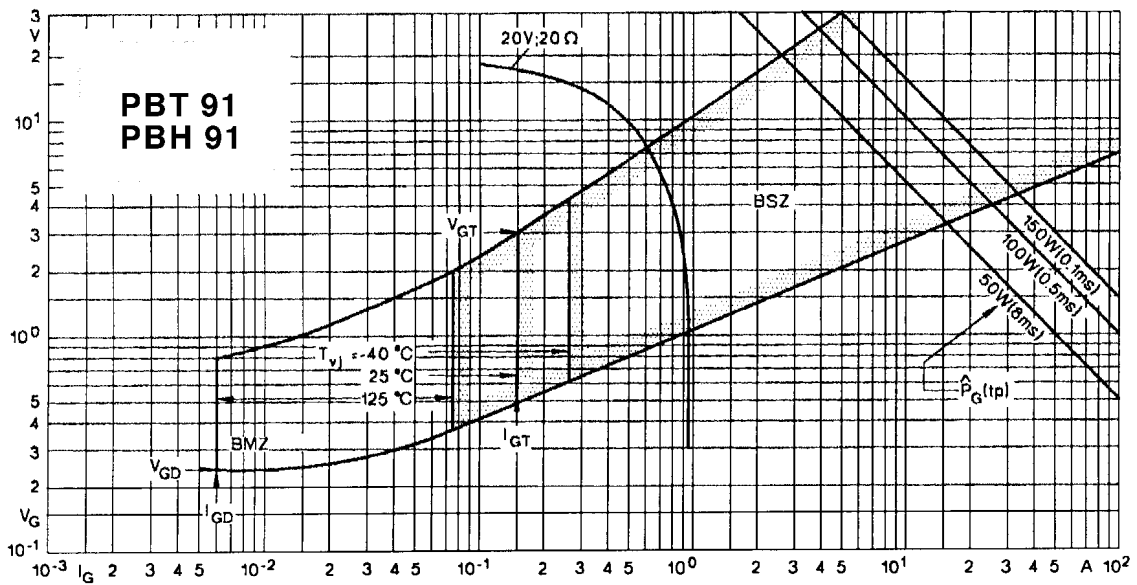


On-state characteristics



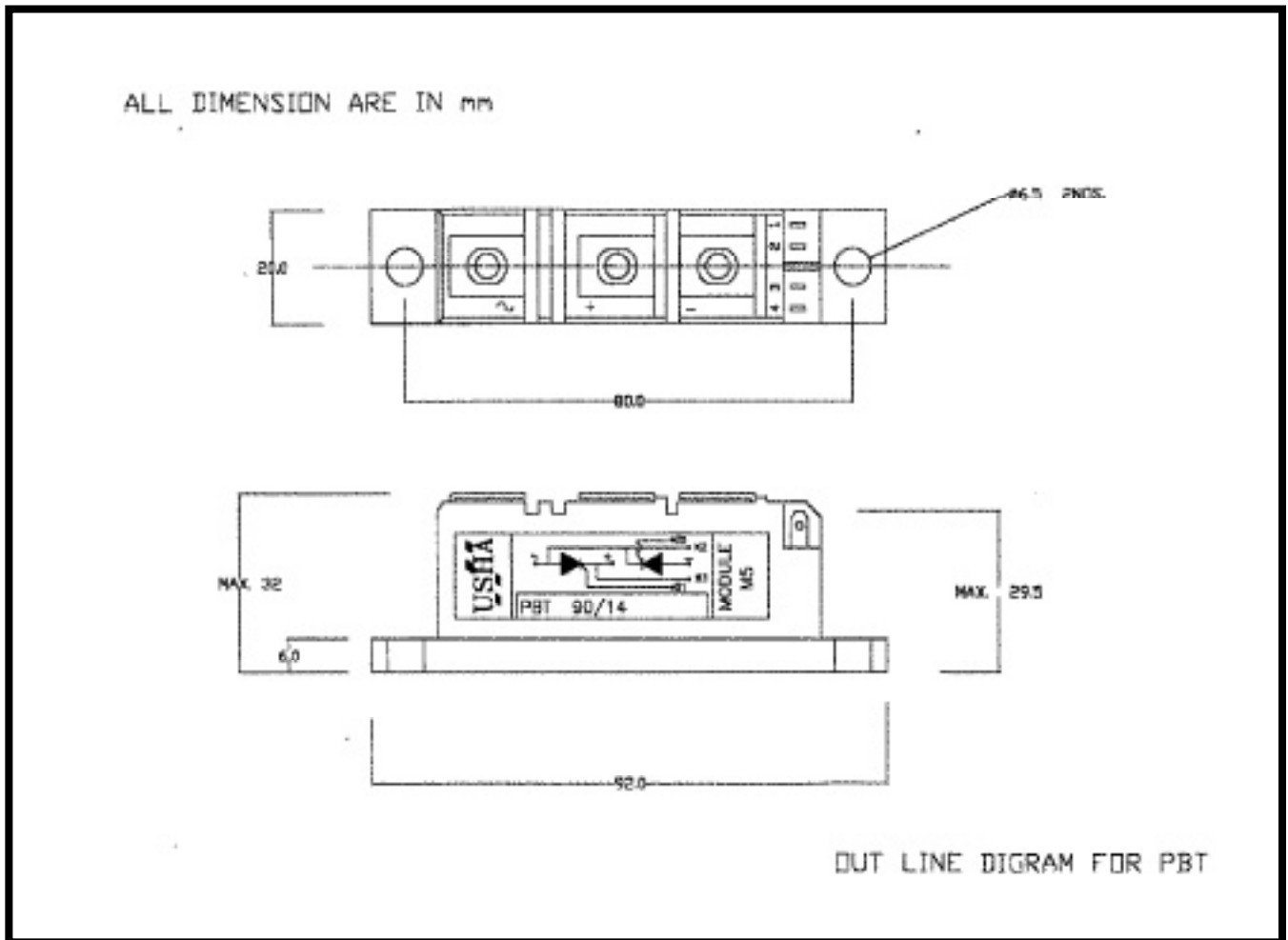
Surge overload current vs. time

\$\$\$ NOTE : If this test is repeated by the user either as a goods inwards check or as a test of the final equipment, in accordance with IEC Publication 146 (1973), clause 492.1, only a voltage slowly increasing up to 3000V a.c. should be used.



Gate trigger characteristics

MECHANICAL DETAILS



ALL DIMENSIONS IN MM
MOUNTING TORQUE CASE TO HEAT SINK = 5 N.M.
MOUNTING TORQUE BUSBARS TO TERMINALS = 3N.M.

MOUNTING INSTRUCTIONS

- GREASE THE BASE PLATE WITH HEAT SINK COMPOUND BEFORE USE.
- MOUNTING TORQUE NOT TO EXCEED 4Nm FOR BOTH THE BOLTS.
- USE ONLY M5 SCREWS.